APPENDIX

Changes to Claims:

Claims 25-27 are added.

The following is a marked-up version of the amended claim(s) 1-24:

1. (Amended) A pyrolytic boron nitride double container for a source of molecular beams used in molecular beam epitaxy, comprising:

an outer container having an outer container transmissivity with respect to light having a wave number of 2600 cm^{-1} to 6500 cm^{-1}, and

an inner container having an inner container transmissivity with respect to light having a wave number of 2600 cm^{-1} to 6500 cm^{-1};

wherein said inner container transmissivity is 90% or less of said outer container transmissivity.~~the transmissivity of an inner container of the pyrolytic boron nitride double container with respect to light having a wave number of 2600 cm^{-1} to 6500 cm^{-1} is 90% or less of that of an outer container.~~

2. (Amended) The pyrolytic boron nitride double container according to Claim 1, said inner container comprising an inner surface and an outer surface;

wherein ~~the~~ said outer surface has a roughness ~~of the outer surface of the inner container is roughened so~~ such that said inner container transmissivity is 90% or less of said outer container transmissivity.~~the transmissivity of the inner container is 90% or less of that of the outer container.~~

3. (Amended) The pyrolytic boron nitride double container according to Claim 1, comprising a doped layer comprising~~wherein an~~ at least one element ~~except nitrogen and boron is~~ doped into ~~the~~ said inner container ~~to form a doped layer,~~;

wherein said at least one element is not selected from the group consisting of nitrogen and boron, and

wherein said doped layer has ~~while~~ at least one of ~~the~~ a thickness, an area, and a doping density ~~of the doped layer is adjusted, so~~such that said inner container transmissivity is 90% or less of said outer container transmissivity. ~~the transmissivity of the inner container is 90% or less of that of the outer container.~~

4. (Amended) The pyrolytic boron nitride double container according to Claim 2, comprising a doped layer comprising ~~wherein an~~at least one element ~~except nitrogen and boron is~~ doped into ~~the~~ said inner container ~~to form a doped layer,~~;

wherein said at least one element is not selected from the group consisting of nitrogen and boron, and

~~while~~wherein said doped layer has at least one of ~~the~~ a thickness, an area, and a doping density ~~of the doped layer is adjusted, so~~ such that said inner container transmissivity is 90% or less of said outer container transmissivity. ~~the transmissivity of the inner container is 90% or less of that of the outer container.~~

5. (Amended) The pyrolytic boron nitride double container according to Claim 3, wherein ~~the~~ said doped layer is located within the inner container, and wherein said doped layer is ~~formed such that the layer is~~ not located~~exposed~~ on ~~neither~~ said inner surface ~~nor~~ said outer surface of ~~the~~ said inner container.

6. (Amended) The pyrolytic boron nitride double container according to Claim 4, wherein ~~the~~ said doped layer is located within the inner container, and wherein said doped layer is ~~formed such that the layer is exposed~~not located on ~~neither~~ said inner surface ~~nor~~ on said outer surface of ~~the~~ said inner container.

7. (Amended) The pyrolytic boron nitride double container according to Claim 3, wherein ~~pyrolytic boron nitride is doped with one or more elements~~ said at least one element is selected from the group consisting of Si, C, and A1.

8. (Amended) The pyrolytic boron nitride double container according to Claim 4, wherein said at least one element is ~~pyrolytic boron nitride is doped with one or more elements~~ selected from the group consisting of Si, C, and Al.

9. (Amended) The pyrolytic boron nitride double container according to Claim 5, wherein said at least one element is~~pyrolytic boron nitride is doped with one or more elements~~ selected from the group consisting of Si, C, and Al.

10. (Amended) The pyrolytic boron nitride double container according to Claim 6, wherein said at least one element is ~~pyrolytic boron nitride is doped with one or more elements~~ selected from the group consisting of Si, C, and Al.

11. (Amended) The pyrolytic boron nitride double container according to Claim 1, wherein ~~the~~ an inner container thickness of ~~the~~ said inner container is ~~increased~~ greater than an outer container thickness of said outer container ~~so~~ such that said inner container transmissivity is 90% or less of said outer container transmissivity.~~the transmissivity of the inner container is 90% or less of that of the outer container.~~

12. (Amended) The pyrolytic boron nitride double container according to Claim 2, wherein ~~the~~ an inner container thickness of ~~the~~ said inner container is ~~increased~~ greater than an outer container thickness of said outer container ~~so~~ such that said inner container transmissivity is 90% or less of said outer container transmissivity.~~the transmissivity of the inner container is 90% or less of that of the outer container.~~

13. (Amended) The pyrolytic boron nitride double container according to Claim 1, wherein said inner container comprises a top, open portion and a bottom portion, and wherein ~~the~~ said inner container transmissivity ~~of the inner container has a profile such that the transmissivity changes~~varies ~~in the height direction of the inner container~~from said bottom portion to said top, open portion.

14. (Amended) The pyrolytic boron nitride double container according to Claim 2, wherein said inner container comprises a top, open portion and a bottom portion, and wherein said inner container ~~the~~ transmissivity varies~~of the inner container has a profile such that the transmissivity changes in the height direction of the inner container~~ from said bottom portion to said top, open portion.

15. (Amended) The pyrolytic boron nitride double container according to Claim 13, wherein said inner container ~~the~~ transmissivity ~~of the inner container~~ decreases ~~at the opening portion of the inner container~~from said bottom portion to said top, open portion.

16. (Amended) The pyrolytic boron nitride double container according to Claim 14, wherein ~~the~~ said inner container transmissivity ~~of the inner container~~ decreases ~~at the opening portion of the inner container~~from said bottom portion to said top, open portion.

17. (Amended) The pyrolytic boron nitride double container according to Claim 13, wherein ~~the~~ said inner container transmissivity ~~of the inner container~~ increases from said bottom portion to said top, open portion~~at the opening portion of the inner container~~.

18. (Amended) The pyrolytic boron nitride double container according to Claim 14, wherein ~~the~~ said inner container transmissivity ~~of the inner container~~ increases from said bottom portion to said top, open portion~~at the opening portion of the inner container~~.

19. (Amended) The pyrolytic boron nitride double container according to Claim 1, ~~wherein there is~~comprising a gap between ~~the~~ said inner container and ~~the~~ said outer container.

20. (Amended) The pyrolytic boron nitride double container according to Claim 2, ~~wherein there is~~comprising a gap between ~~the~~ said inner container and ~~the~~ said outer container.

21. (Amended) The pyrolytic boron nitride double container according to Claim 19, wherein ~~the~~ said gap ~~between the inner container and the outer container~~ is 0.2 to 30 mm.

22. (Amended) The pyrolytic boron nitride double container according to Claim 20, wherein ~~the~~ said gap ~~between the inner container and the outer container~~ is 0.2 to 30 mm.

23. (Amended) A method of manufacturing a pyrolytic boron nitride double container for a source of molecular beams used in molecular beam epitaxy, comprising:

~~wherein~~ forming an inner container and an outer container ~~of the pyrolytic boron nitride double container are formed~~ by a CVD reaction,

roughening ~~the~~ an outer surface of the ~~formed~~ inner container ~~is roughened to~~, thereby adjusting ~~the~~ an amount of light scattered at the outer surface, and

setting ~~such that the~~ an inner container transmissivity ~~of the inner container~~ with respect to light having a wave number of 2600 cm^{-1} to 6500 cm^{-1} ~~is set~~ to 90% or less of ~~that of the~~ an outer container transmissivity, with respect to light having a wave number of 2600 cm^{-1} to 6500 cm^{-1}.

24. (Amended) A method of manufacturing a pyrolytic boron nitride double container for a source of molecular beams used in molecular beam epitaxy, comprising:

depositing ~~in which~~ pyrolytic boron nitride ~~is deposited~~ on a graphite mandrel by a CVD reaction, thereby ~~in order to~~ forming the double container,

~~and the double container is then separated from the mandrel, wherein~~ forming a doped layer in the pyrolytic boron nitride container by introducing a dopant gas ~~is introduced~~ during the CVD reaction of the inner container ~~in order to form a doped layer in the pyrolytic boron nitride container~~,

adjusting ~~and~~ at least one of the thickness, area and the doping density of the doped layer ~~is adjusted so as to~~,

setting the inner container transmissivity ~~of the inner container~~ with respect to light having a wave number of 2600 cm^{-1} to 6500 cm^{-1} to 90% or less of ~~that of the~~ an outer container transmissivity, with respect to light having a wave number of 2600 cm^{-1} to 6500 cm^{-1}, and

separating the double container from the mandrel.